Low-power dual 2-input NAND gate; open drain Rev. 8 — 11 February 2013 Pr

Product data sheet

General description 1.

The 74AUP2G38 provides the dual 2-input NAND gate with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \,\mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

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3. Ordering information

g information								
Package	Package							
Temperature range	Name	Description	Version					
–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1					
–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 \times 1.95 \times 0.5 mm	SOT833-1					
–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1 \times 0.5 mm	SOT1089					
–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2					
–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2					
–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116					
–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 \times 1.0 \times 0.35 mm	SOT1203					
	Package Temperature range -40 °C to +125 °C -40 °C to +125 °C	Package Temperature range Name -40 °C to +125 °C VSSOP8 -40 °C to +125 °C XSON8 -40 °C to +125 °C XSON8	PackageTemperature rangeNameDescription-40 °C to +125 °CVSSOP8plastic very thin shrink small outline package; 8 leads; body width 2.3 mm-40 °C to +125 °CXSON8plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm-40 °C to +125 °CXSON8plastic extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm-40 °C to +125 °CXSON8plastic extremely thin small outline package; no leads; 8 terminals; body 3 × 2 × 0.5 mm-40 °C to +125 °CXQFN8plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 × 1.6 × 0.5 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm-40 °C to +125 °CXSON8extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm					

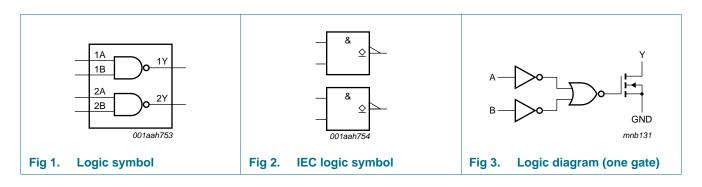
4. Marking

Table 2.Marking codes

3 1 1 1	
Type number	Marking code ^[1]
74AUP2G38DC	a38
74AUP2G38GT	a38
74AUP2G38GF	aB
74AUP2G38GD	a38
74AUP2G38GM	a38
74AUP2G38GN	aB
74AUP2G38GS	aB

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

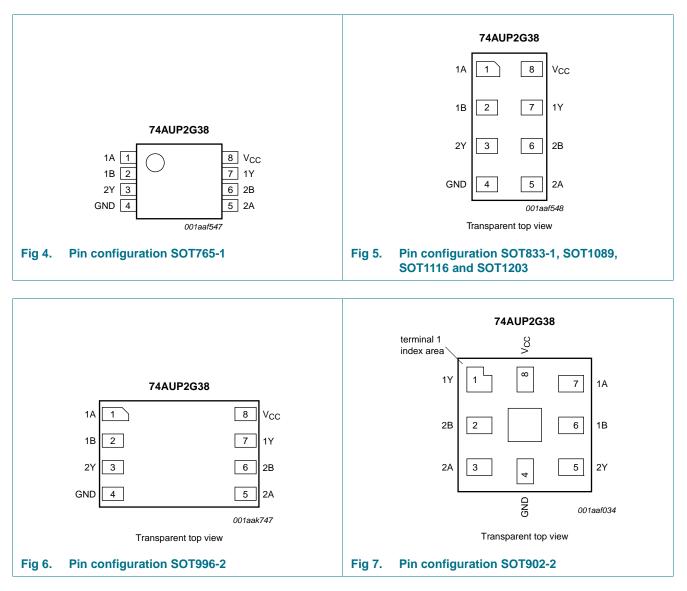
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Symbol	Pin		Description		
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2			
1A, 2A	1, 5	7, 3	data input		
1B, 2B	2, 6	6, 2	data input		
GND	4	4	ground (0 V)		
1Y, 2Y	7, 3	1, 5	data output		
V _{CC}	8	8	supply voltage		
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7. Functional description

	Table 4	4.	Function	table ^[1]
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Input		Output
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

[1] H = HIGH voltage level;

L = LOW voltage level;

Z = high-impedance OFF state.

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
Ι _Ο	output current	$V_{O} = 0 V \text{ to } V_{CC}$	-	+20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \text{ to } +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of Ptot derates linearly at 8.0 mW/K.

For XSON8 and XQFN8 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Operating conditions				
Parameter	Conditions	Min	Max	Unit
supply voltage		0.8	3.6	V
input voltage		0	3.6	V
output voltage	Active mode and Power-down mode	0	3.6	V
ambient temperature		-40	+125	°C
input transition rise and fall rate	$V_{CC} = 0.8 \text{ V} \text{ to } 3.6 \text{ V}$	0	200	ns/V
	Parameter supply voltage input voltage output voltage ambient temperature	Parameter Conditions supply voltage input voltage output voltage Active mode and Power-down mode ambient temperature Image: Conditions	Parameter Conditions Min supply voltage 0.8 input voltage 0 output voltage Active mode and Power-down mode 0 ambient temperature -40	ParameterConditionsMinMaxsupply voltage0.83.6input voltage03.6output voltageActive mode and Power-down mode03.6ambient temperature-40+125

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
VIH HIGH-level input voltage		$V_{CC} = 0.8 V$	0.70V _{CC}	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	0.30V _{CC}	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35V_{CC}$	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
l _l	input leakage current	V_1 = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
I _{OZ}	OFF-state output current	$ V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 0 \text{ V to } 3.6 \text{ V}; \\ V_{CC} = 0 \text{ V to } 3.6 \text{ V} $	-	-	±0.1	μA
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \text{ to } \ 3.6 \ V \end{array}$	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 0.6 \; V; \; I_{O} = 0 \; A; \\ V_{CC} = 3.3 \; V \end{array}$	-	-	40	μΑ
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_{I} = GND or V_{CC}	-	0.7	-	pF
Co	output capacitance	$V_{O} = GND; V_{CC} = 0 V$	-	0.9	-	pF

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C					
VIH	HIGH-level input voltage	$V_{CC} = 0.8 V$	$0.70V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	0.65V _{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	0.30V _{CC}	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I _I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
I _{OZ}	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μA
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I _{CC}	supply current	$V_{I} = GND \text{ or } V_{CC}; I_{O} = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
ΔI_{CC}	additional supply current	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ

Table 7. Static characteristics ... continued

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<u> </u>	– <i>i</i>	A 11/1		-		
	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	-40 °C to +125 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75V_{CC}$	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.70V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	0.30V _{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = 20 µA; V_{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33V_{CC}$	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
I _I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μA
I _{OZ}	OFF-state output current	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±0.75	μA
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \text{ to } 3.6 \ V \end{array}$	-	-	1.4	μA
ΔI_{CC}	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 0.6 \; V; \; I_{O} = 0 \; A; \\ V_{CC} = 3.3 \; V \end{array}$	-	-	75	μΑ

Table 7. Static characteristics ... continued

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		–40 °C to +125 °C			Unit	
			Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)		
C _L = 5 pl	=									
t _{pd}	propagation delay	nA, nB to nY; see Figure 8	2 <u>]</u>							
		$V_{CC} = 0.8 V$	-	13.5	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	1.9	4.6	10.4	1.8	11.4	12.6	ns	
		V_{CC} = 1.4 V to 1.6 V	1.5	3.3	6.5	1.4	7.4	8.2	ns	
		V_{CC} = 1.65 V to 1.95 V	1.2	2.9	5.1	1.1	5.9	6.5	ns	
		V_{CC} = 2.3 V to 2.7 V	1.0	2.2	3.8	0.9	4.5	4.9	ns	
		V_{CC} = 3.0 V to 3.6 V	0.9	2.3	4.0	0.8	4.5	4.9	ns	
C _L = 10 p	ρF									
t _{pd}	propagation delay	nA, nB to nY; see Figure 8	2]							
		V _{CC} = 0.8 V	-	16.3	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	2.3	5.6	12.3	2.1	13.7	15.1	ns	
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	1.8	4.1	7.6	1.7	8.8	9.7	ns	
		V _{CC} = 1.65 V to 1.95 V	1.6	3.8	6.1	1.4	7.1	7.8	ns	
		V_{CC} = 2.3 V to 2.7 V	1.4	2.9	4.6	1.2	5.4	5.9	ns	
		V_{CC} = 3.0 V to 3.6 V	1.3	3.2	5.7	1.1	6.4	7.0	ns	
C _L = 15 p	ρF									
pd	propagation delay	nA, nB to nY; see Figure 8	2]							
		$V_{CC} = 0.8 V$	-	19.0	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	2.6	6.6	14.2	2.4	15.8	17.4	ns	
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$	2.1	4.8	8.7	1.9	10.1	11.1	ns	
		V _{CC} = 1.65 V to 1.95 V	1.9	4.6	7.6	1.7	8.5	9.3	ns	
		V_{CC} = 2.3 V to 2.7 V	1.6	3.6	5.6	1.5	6.3	6.9	ns	
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.6	4.1	7.5	1.4	8.3	9.1	ns	
C _L = 30 p	ρF									
pd	propagation delay	nA, nB to nY; see Figure 8	2]							
		$V_{CC} = 0.8 V$	-	27.0	-	-	-	-	ns	
		$V_{CC} = 1.1 \text{ V} \text{ to } 1.3 \text{ V}$	3.6	9.5	19.5	3.2	21.8	24.0	ns	
		V_{CC} = 1.4 V to 1.6 V	2.9	7.0	11.5	2.6	13.6	15.0	ns	
		V_{CC} = 1.65 V to 1.95 V	2.6	7.0	12.1	2.3	13.3	14.6	ns	
		V_{CC} = 2.3 V to 2.7 V	2.4	5.4	8.9	2.1	9.9	10.9	ns	

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Dynamic characteristics ... continued Table 8.

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions	25 °C			-4	Unit		
			Min	Typ[1]	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pF	, 10 pF, 15 pF and 3	ю рF					1		
C _{PD}	power dissipation capacitance	f = 1 MHz; V_I = GND to V_{CC}	[3]						
		$V_{CC} = 0.8 V$	-	0.6	-	-	-	-	pF
		V_{CC} = 1.1 V to 1.3 V	-	0.7	-	-	-	-	pF
		V_{CC} = 1.4 V to 1.6 V	-	0.8	-	-	-	-	pF
		V_{CC} = 1.65 V to 1.95 V	-	0.9	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V	-	1.1	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	1.4	-	-	-	-	рF

[1] All typical values are measured at nominal V_{CC} .

[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

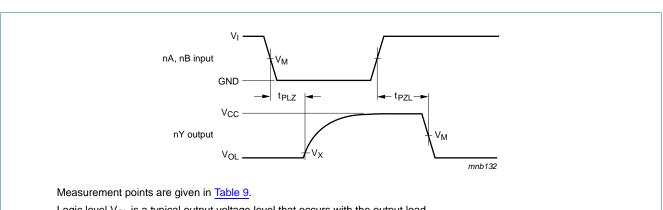
 P_{D} = $C_{PD} \times V_{CC}{}^2 \times f_i \times N$ where:

 f_i = input frequency in MHz;

V_{CC} = supply voltage in V;

N = number of inputs switching.

12. Waveforms



Logic level V_{OL} is a typical output voltage level that occurs with the output load.

Fig 8. The data input (nA, nB) to output (nY) propagation delays

Table 9. **Measurement points**

Supply voltage	Input	Output	
V _{cc}	V _M	V _M	V _X
0.8 V to 1.6 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.1 V
1.65 V to 2.7 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V
3.0 V to 3.6 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V

74AUP2G38 **Product data sheet**

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Low-power dual 2-input NAND gate; open drain

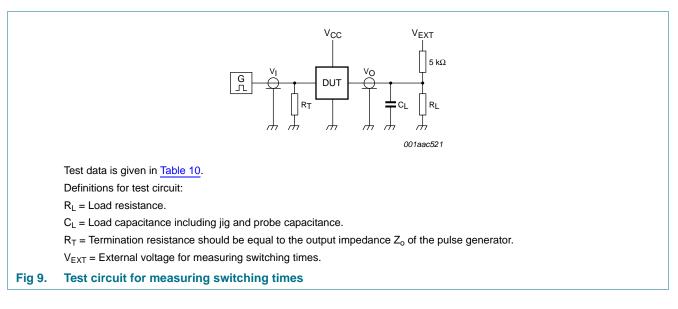


Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{cc}	CL	RL ^[1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	2V _{CC}

[1] For measuring enable and disable times $R_L = 5 k\Omega$.

For measuring propagation delays, set-up times, hold times and pulse width, R_L = 1 M Ω .

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13. Package outline

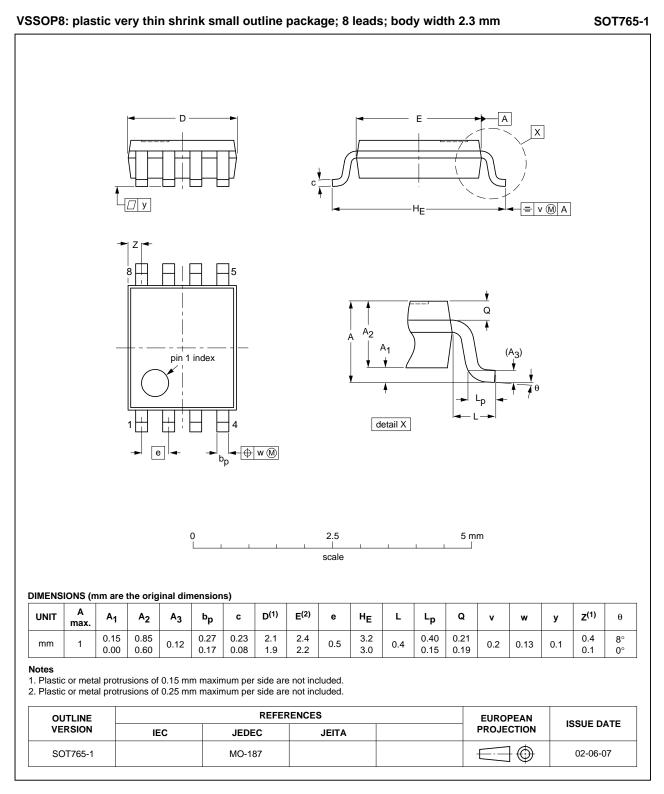


Fig 10. Package outline SOT765-1 (VSSOP8)

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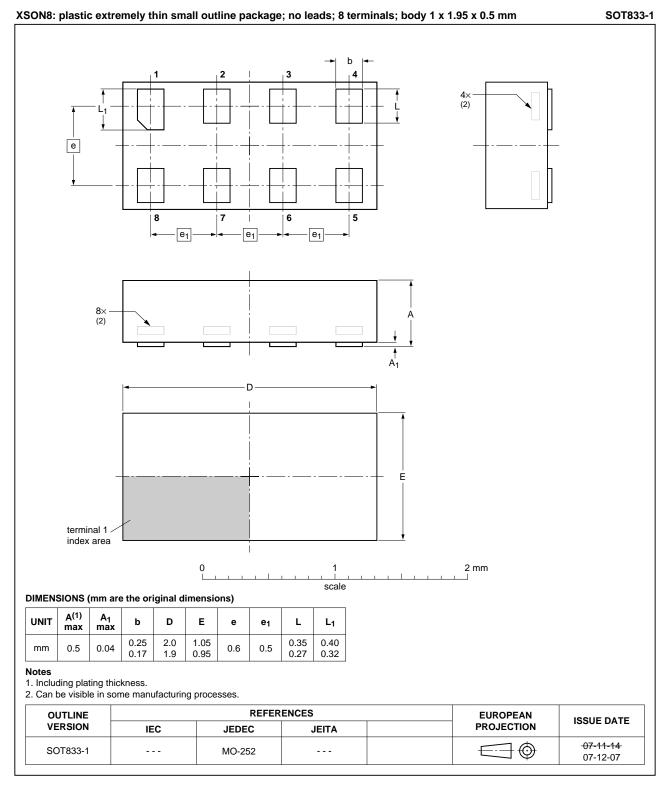
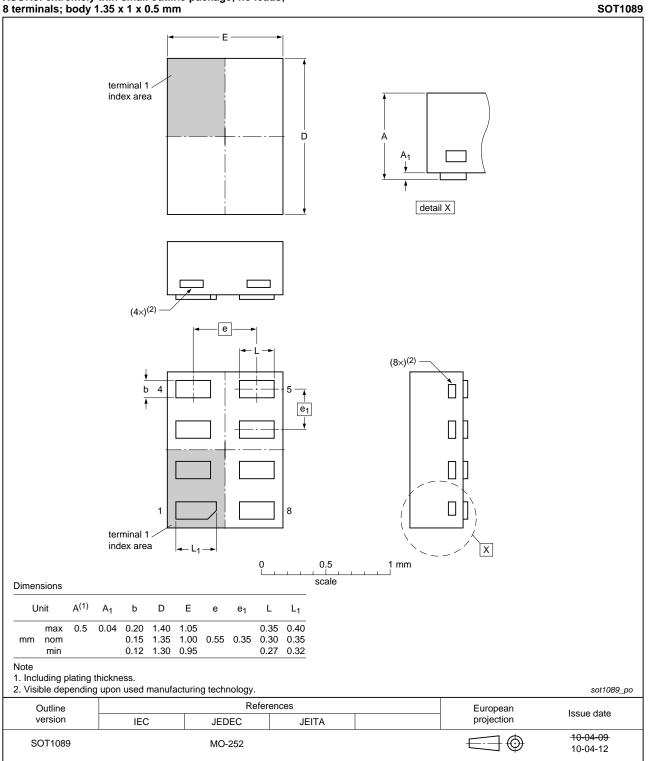


Fig 11. Package outline SOT833-1 (XSON8)

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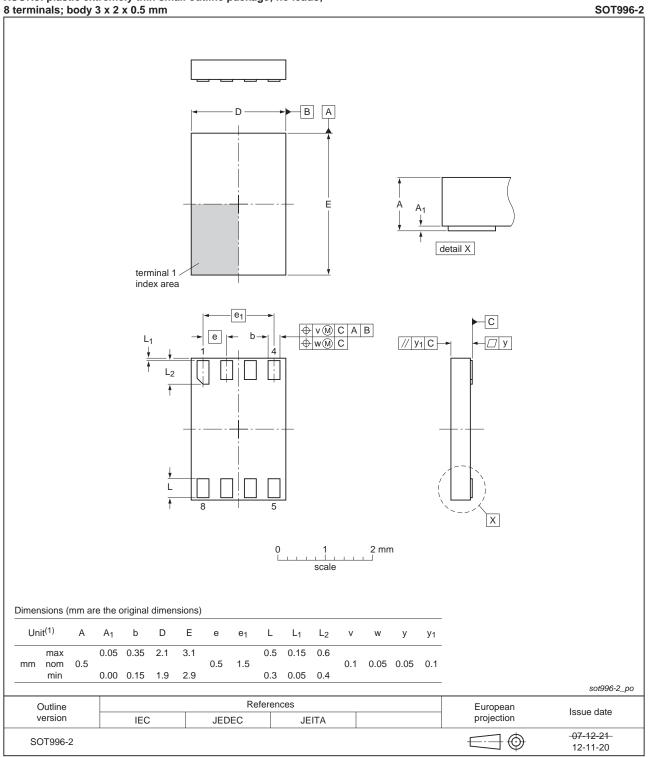


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

Fig 12. Package outline SOT1089 (XSON8)

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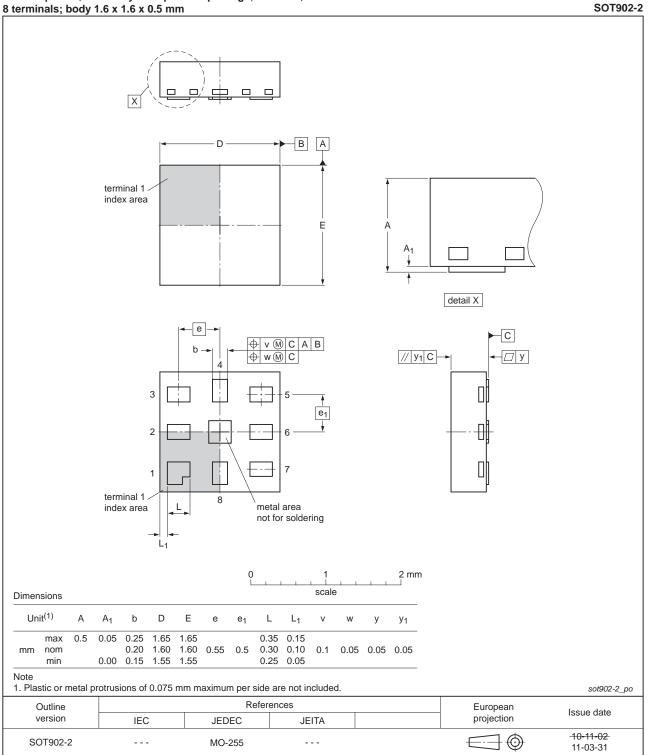


XSON8: plastic extremely thin small outline package; no leads;

Fig 13. Package outline SOT996-2 (XSON8)

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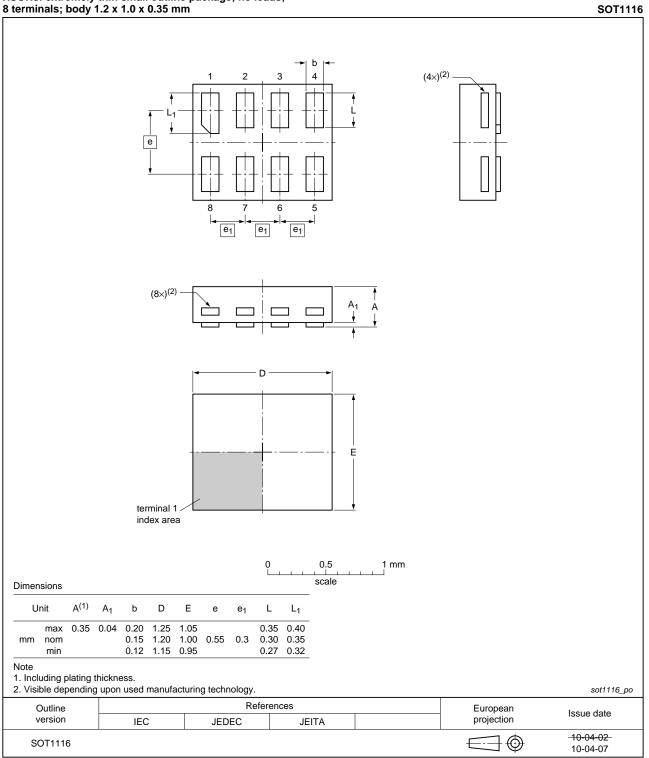


XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

Fig 14. Package outline SOT902-2 (XQFN8)

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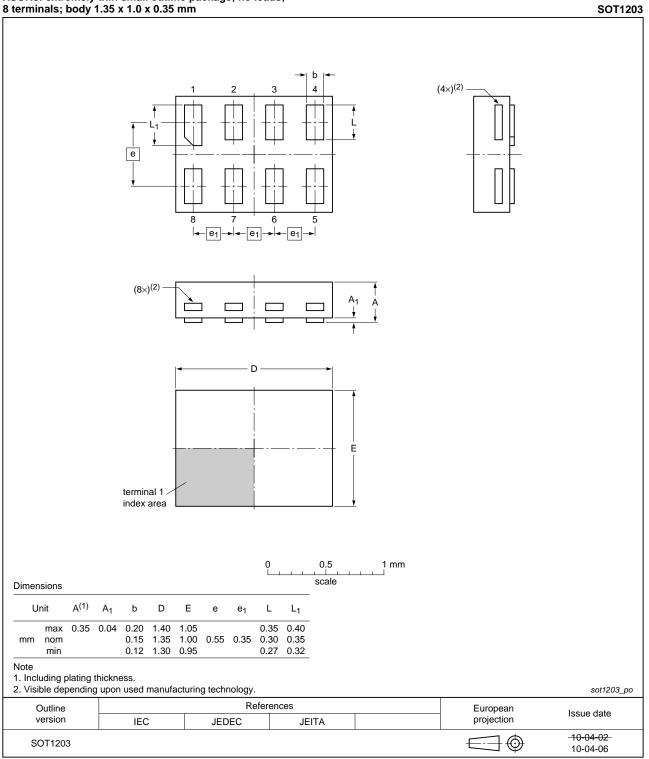


XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1116 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1203 (XSON8)

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14. Abbreviations

Table 11. Abbreviations		
Acronym	Description	
CDM	Charged Device Model	
DUT	Device Under Test	
ESD	ElectroStatic Discharge	
HBM	Human Body Model	
MM	Machine Model	
MM	Machine Model	

15. Revision history

ory			
Release date	Data sheet status	Change notice	Supersedes
20130211	Product data sheet	-	74AUP2G38 v.7
 For type num 	ber 74AUP2G38GD XSON8U	has changed to XS	ON8.
20120605	Product data sheet	-	74AUP2G38 v.6
20111209	Product data sheet	-	74AUP2G38 v.5
20100923	Product data sheet	-	74AUP2G38 v.4
20091008	Product data sheet	-	74AUP2G38 v.3
20090616	Product data sheet	-	74AUP2G38 v.2
20080312	Product data sheet	-	74AUP2G38 v.1
20061016	Product data sheet	-	-
	Release date 20130211 • For type num 20120605 20111209 20100923 20091008 20090616 20080312	Release dateData sheet status20130211Product data sheet• For type number 74AUP2G38GD XSON8U20120605Product data sheet20111209Product data sheet20100923Product data sheet20091008Product data sheet20090616Product data sheet20080312Product data sheet	Release dateData sheet statusChange notice20130211Product data sheet-• For type number 74AUP2G38GD XSON8U has changed to XS20120605Product data sheet-20111209Product data sheet-20100923Product data sheet-20091008Product data sheet-20090616Product data sheet-20080312Product data sheet-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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